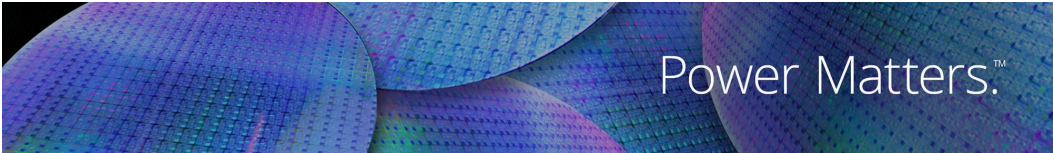


POWER DISCRETES & MODULES

- ▶ Voltage & Current Regulation Diodes
- ▶ Small Signal Diodes and Diode Arrays
- ▶ IGBT
- ▶ Power MOSFET
- ▶ Power Modules
- ▶ JFET
- ▶ BJT (BiPolar Junction Transistor)
- ▶ Legacy Power Discretes & Modules
- ▶ Diode and Rectifier Devices
- ▶ Silicon Carbide (SiC) Semiconductor
 - SiC Schottky Barrier Diodes
 - ▶ SiC Modules
 - SiC MOSFET



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MSC140SMA120B

Product Status

■ Sampling

Overview

Resources

Diagrams

Ordering

Support

Silicon carbide (SiC) power MOSFET product line from Microsemi increases your performance over silicon MOSFET and silicon IGBT solutions while lowering your total cost of ownership for high-voltage applications.
Silicon Carbide N-Channel Power MOSFET, 1200V, 140 mΩ



ROHS

Package Tube
Carrier:

Electrical Rating	Symbol	Min	Typ	Max	Unit
On-State Resistance (milliohms)	$R_{DS(on)}$		140	175	mΩ

Environmental Rating	Symbol	Min	Typ	Max	Unit
Junction Temperature (°C)	T_J	-55		175	°C

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)}$			1200	V

This part can be found in the following product categories:

- Power Discretes & Modules ▶ Silicon Carbide (SiC) Semiconductor ▶ SiC MOSFET